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(71) Applicant: MICRON TECHNOLOGY, INC. [US/US]; 8000 S. Federal Way, Boise, Idaho 83707-0006 (US).

(72) Inventors: YATES, Donald, L.; 11151 Musket Street, Boise, ID 83715 (US). DREWES, Joel, A.; 1920 Harrison Blvd., Boise, ID 83702 (US).

(74) Agent: D'AMICO, Thomas, J.; Dickstein Shapiro Morin & Oshinsky LLP, 2101 L Street, N.W., Washington, DC 20037-1526 (US).

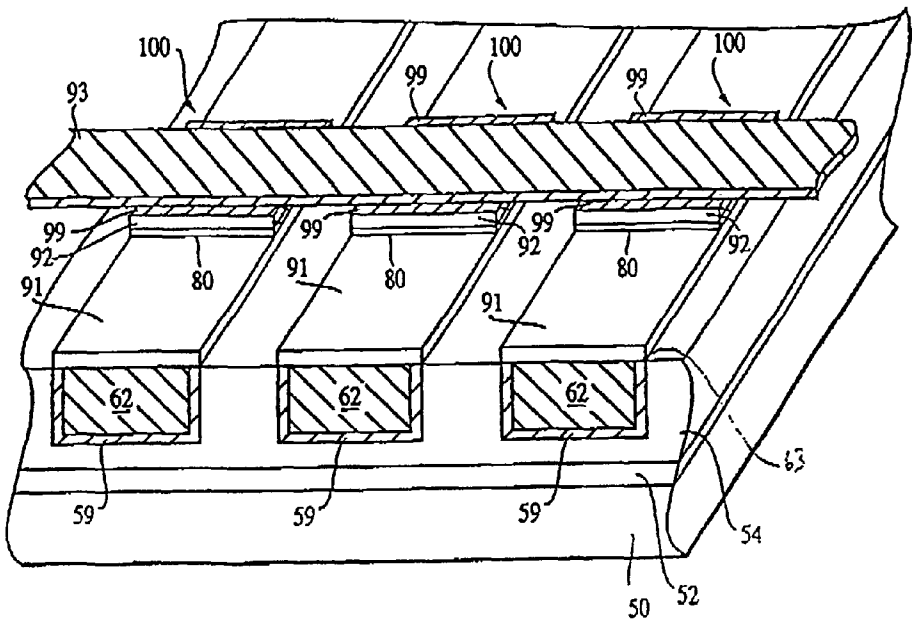
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(54) Title: A METHOD OF IMPROVING SURFACE PLANARITY PRIOR TO MRAM BIT MATERIAL DEPOSITION



(57) Abstract: The present invention provides a method of fabricating a portion of a memory cell, the method comprising providing a first conductor in a trench which is provided in an insulating layer and flattening an upper surface of the insulating layer and the first conductor, forming a material layer over the flattened upper surface of the insulating layer and the first conductor and flattening an upper portion of the material layer while leaving intact a lower portion of the material layer over the insulating layer and the first conductor.

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